_M10 Operational Amplifier and Voltage Reference

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LM10 Operational Amplifier and Voltage Reference

General Description

The LM10 series are monolithic linear ICs consisting of a precision reference, an adjustable reference buffer and an independent, high quality op amp.

The unit can operate from a total supply voltage as low as 1.1V or as high as 40V, drawing only 270μ A. A complementary output stage swings within 15 mV of the supply terminals or will deliver ±20 mA output current with ±0.4V saturation. Reference output can be as low as 200 mV.

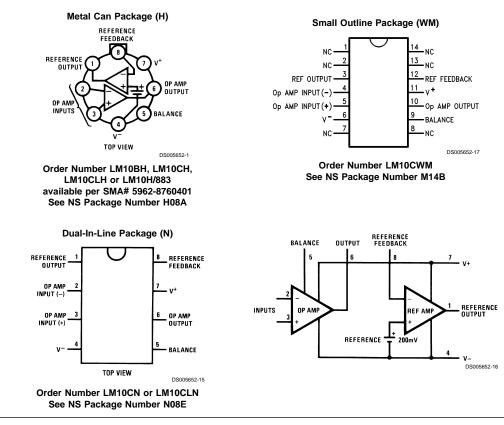
The circuit is recommended for portable equipment and is completely specified for operation from a single power cell. In contrast, high output-drive capability, both voltage and current, along with thermal overload protection, suggest it in demanding general-purpose applications.

The device is capable of operating in a floating mode, independent of fixed supplies. It can function as a remote comparator, signal conditioner, SCR controller or transmitter for analog signals, delivering the processed signal on the same line used to supply power. It is also suited for operation in a wide range of voltage- and current-regulator applications, from low voltages to several hundred volts, providing greater precision than existing ICs.

This series is available in the three standard temperature ranges, with the commercial part having relaxed limits. In addition, a low-voltage specification (suffix "L") is available in the limited temperature ranges at a cost savings.

Features

- input offset voltage: 2.0 mV (max)
- input offset current: 0.7 nA (max)
- input bias current: 20 nA (max)
- reference regulation: 0.1% (max)
- offset voltage drift: 2µV/°C
- reference drift: 0.002%/°C



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Connection and Functional Diagrams

Absolute Maximum Ratings (Notes 1, 8)

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If Military/Aerospace specified devices are required, please contact the National Semiconductor Sales Office/ Distributors for availability and specifications.

	LM10/LM10B/ LM10C	LM10BL/ LM10CL
Total Supply Voltage	45V	7V
Differential Input Voltage (Note 2)	±40V	±7V
Power Dissipation (Note 3)	internally li	mited
Output Short-circuit Duration (Note 4)	continuo	ous
Storage-Temp. Range	–55°C to +	150°C
Lead Temp. (Soldering, 10 seconds)		
Metal Can	300°C	;
Lead Temp. (Soldering, 10 seconds) DIP	260°C	;
Vapor Phase (60 seconds)	215°C	;
Infrared (15 seconds)	220°C	;

See AN-450 "Surface Mounting Methods and Their Effect on Product Reliability" for other methods of soldering surface mount devices.

Electrical Characteristics

 Maximum Junction Temperature

 LM10
 150°C

 LM10B
 100°C

 LM10C
 85°C

Operating Ratings

ESD rating is to be determined.

Package Thermal Resistance	
θ _{JA}	
H Package	150°C/W
N Package	87°C/W
WM Package	90°C/W
θ _{JC}	
H Package	45°C/W

Parameter	Conditions	LM10/LM10B			LM10C			Units
		Min	Тур	Max	Min	Тур	Max	1
Input offset voltage			0.3	2.0		0.5	4.0	mV
				3.0			5.0	mV
Input offset current			0.25	0.7		0.4	2.0	nA
(Note 6)				1.5			3.0	nA
Input bias current			10	20		12	30	nA
				30			40	nA
Input resistance		250	500		150	400		kΩ
		150			115			kΩ
Large signal voltage	$V_{S}=\pm 20V, I_{OUT}=0$	120	400		80	400		V/mV
gain	V _{OUT} =±19.95V	80			50			V/mV
	$V_{S}=\pm 20V, V_{OUT}=\pm 19.4V$	50	130		25	130		V/mV
	I _{OUT} =±20 mA (±15 mA)	20			15			V/mV
	V _S =±0.6V (0.65V) , I _{OUT} =±2 mA	1.5	3.0		1.0	3.0		V/mV
	V _{OUT} =±0.4V (±0.3V), V _{CM} =-0.4V	0.5			0.75			V/mV
Shunt gain (Note 7)	1.2V (1.3V) ≤V _{OUT} ≤40V,	14	33		10	33		V/mV
	$R_L=1.1 \ k\Omega$							
	0.1 mA≤l _{o∪⊤} ≤5 mA	6			6			V/mV
	1.5V≤V ⁺ ≤40V, R _L =250Ω	8	25		6	25		V/mV
	0.1 mA≤I _{OUT} ≤20 mA	4			4			V/mV
Common-mode	–20V≤V _{CM} ≤19.15V (19V)	93	102		90	102		dB
rejection	V _S =±20V	87			87			dB
Supply-voltage	–0.2V≥V [–] ≥–39V	90	96		87	96		dB
rejection	V ⁺ =1.0V (1.1V)	84			84			dB
	1.0V (1.1V) ≤V ⁺ ≤39.8V	96	106		93	106		dB
	V ⁻ =-0.2V	90			90			dB
Offset voltage drift			2.0			5.0		µV/°C
Offset current drift			2.0			5.0		pA/°C
Bias current drift	T _C <100°C		60			90		pA/°C
Line regulation	1.2V (1.3V) ≤V _S ≤40V		0.001	0.003		0.001	0.008	%/V
	0≤I _{REF} ≤1.0 mA, V _{REF} =200 mV			0.006			0.01	%/V

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T _J =25°C, T _{MIN} ≤T _J ≤T _{MAX} Parameter	x (Boldface type refers to limits over	LM10/LM10B			1			
	Conditions	Min		Мах	Min	LM10C	Мах	Units
Load regulation	0≤I _{RFF} ≤1.0 mA	WIIII	Typ 0.01	0.1	IVIIII	Typ 0.01	0.15	%
Load regulation	V ⁺ −V _{REF} ≥1.0V (1.1V)		0.01	0.15		0.01	0.10 0.2	%
Amplifier gain	0.2V≤V _{REF} ≤35V	50	75	0.15	25	70	0.2	70 V/m\
	0.2 V = V REF=00 V	23	/5		15			V/mV
Feedback sense		195	200	205	190	200	210	mV
voltage		194	200	200 206	189	200	210	mV
Feedback current			20	50		22	75	nA
				65			90	nA
Reference drift			0.002			0.003		%/°C
Supply current			270	400		300	500	μA
			-	500			570	μA
Supply current change	1.2V (1.3V) ≤V _S ≤40V		15	75		15	75	μA
Parameter	x (Boldface type refers to limits over Conditions	Min	LM10BL Typ		Min	LM10CL Typ	Max	Units
1		Min			Min			
Input offset voltage			0.3	2.0 3.0		0.5	4.0 5.0	mV mV
Input offset current		-	0.1	0.7		0.2	2.0	nA
(Note 6)			0.1	1.5		0.2	2.0 3.0	nA
Input bias current			10	20		12	30	nA
input bias current				30		12	40	nA
Input resistance		250	500		150	400		kΩ
		150			115			kΩ
Large signal voltage	V _S =±3.25V, I _{OUT} =0	60	300		40	300		V/m\
gain	$V_{OUT}=\pm 3.2V$	40			25			V/m\
	V _S =±3.25V, I _{OUT} =10 mA	10	25		5	25		V/m\
	V _{OUT} =±2.75 V	4			3			V/m\
	V _S =±0.6V (0.65V) , I _{OUT} =±2 mA	1.5	3.0		1.0	3.0		V/m\
	V _{OUT} =±0.4V (±0.3V), V _{CM} =-0.4V	0.5			0.75			V/m\
Shunt gain (Note 7)	1.5V≤V ⁺ ≤6.5V, R _L =500Ω	8	30		6	30		V/m\
	0.1 mA≤I _{OUT} ≤10 mA	4			4			V/m\
Common-mode	-3.25V≤V _{CM} ≤2.4V (2.25V)	89	102		80	102		dB
rejection	$V_{\rm S} = \pm 3.25 V$	83			74			dB
Supply-voltage	-0.2V≥V ⁻ ≥-5.4V V ⁺ =1.0V (1.2V)	86	96		80	96		dB
rejection	V ⁺ =1.0V (1.2V) 1.0V (1.1V) ≤V ⁺ ≤6.3V	80 94	106		74 80	106		dB dB
	V ⁻ =0.2V	88	100		74	100		dB
Offset voltage drift	V -0.2V	00	2.0		/4	5.0		μV/°C
Offset current drift			2.0			5.0		pΑ/°C
Bias current drift			60			90		p/v c
	1.2V (1.3V) ≤V _S ≤6.5V		0.001	0.01		0.001	0.02	%/V
Line regulation				0.02			0.03	%/V
Line regulation	0≤I _{RFF} ≤0.5 mA, V _{RFF} =200 mV				1	1		
Line regulation	$0 \le I_{REF} \le 0.5 \text{ mA}, V_{REF} = 200 \text{ mV}$ $0 \le I_{REF} \le 0.5 \text{ mA}$		0.01	0.1		0.01	0.15	%

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 $T_J=25^{\circ}C$, $T_{MIN} \leq T_J \leq T_{MAX}$ (Boldface type refers to limits over temperature range) (Note 5)

Parameter	Conditions	LM10BL			LM10CL			Units
		Min	Тур	Max	Min	Тур	Max	
Amplifier gain	0.2V≤V _{REF} ≤5.5V	30	70		20	70		V/mV
		20			15			V/mV
Feedback sense voltage		195	200	205	190	200	210	mV
		194		206	189		211	mV
Feedback current			20	50		22	75	nA
				65			90	nA
Reference drift			0.002			0.003		%/°C
Supply current			260	400		280	500	μA
				500			570	μA

Note 1: Absolute Maximum Ratings indicate limits beyond which damage to the device may occur. Operating Ratings indicate conditions for which the device is functional, but do not guarantee specific performance limits.

Note 2: The Input voltage can exceed the supply voltages provided that the voltage from the input to any other terminal does not exceed the maximum differential input voltage and excess dissipation is accounted for when $V_{IN} < V^-$.

Note 3: The maximum, operating-junction temperature is 150°C for the LM10, 100°C for the LM10B(L) and 85°C for the LM10C(L). At elevated temperatures, devices must be derated based on package thermal resistance.

Note 4: Internal thermal limiting prevents excessive heating that could result in sudden failure, but the IC can be subjected to accelerated stress with a shorted output and worst-case conditions.

Note 5: These specifications apply for $V^- \le V_{CM} \le V^+ - 0.85V$ (1.0V), 1.2V (1.3V) $< V_S \le V_{MAX}$. $V_{REF} = 0.2V$ and $0 \le I_{REF} \le 1.0$ mA, unless otherwise specified: $V_{MAX} = 40V$ for the standard part and 6.5V for the low voltage part. Normal typeface indicates 25'C limits. Boldface type indicates limits and altered test conditions for full-temperature-range operation; this is -55'C to 125'C for the LM10, -25'C to 85'C for the LM10B(L) and 0'C to 70'C for the LM10C(L). The specifications do not include the effects of thermal gradients ($\tau_1 \equiv 20$ ms), die heating ($\tau_2 \equiv 0.2s$) or package heating. Gradient effects are small and tend to offset the electrical error (see curves).

Note 6: For $T_J > 90^{\circ}$ C, I_{OS} may exceed 1.5 nA for $V_{CM} = V^-$. With $T_J = 125^{\circ}$ C and $V^- \leq V_{CM} \leq V^- + 0.1$ V, $I_{OS} \leq 5$ nA.

Note 7: This defines operation in floating applications such as the bootstrapped regulator or two-wire transmitter. Output is connected to the V⁺ terminal of the IC and input common mode is referred to V⁻ (see typical applications). Effect of larger output-voltage swings with higher load resistance can be accounted for by adding the positive-supply rejection error.

Note 8: Refer to RETS10X for LM10H military specifications.

Definition of Terms

Input offset voltage: That voltage which must be applied between the input terminals to bias the unloaded output in the linear region.

Input offset current: The difference in the currents at the input terminals when the unloaded output is in the linear region.

Input bias current: The absolute value of the average of the two input currents.

Input resistance: The ratio of the change in input voltage to the change in input current on either input with the other grounded.

Large signal voltage gain: The ratio of the specified output voltage swing to the change in differential input voltage required to produce it.

Shunt gain: The ratio of the specified output voltage swing to the change in differential input voltage required to produce it with the output tied to the V⁺ terminal of the IC. The load and power source are connected between the V⁺ and V⁻ terminals, and input common-mode is referred to the V⁻ terminal.

Common-mode rejection: The ratio of the input voltage range to the change in offset voltage between the extremes.

Supply-voltage rejection: The ratio of the specified supply-voltage change to the change in offset voltage between the extremes.

Line regulation: The average change in reference output voltage over the specified supply voltage range.

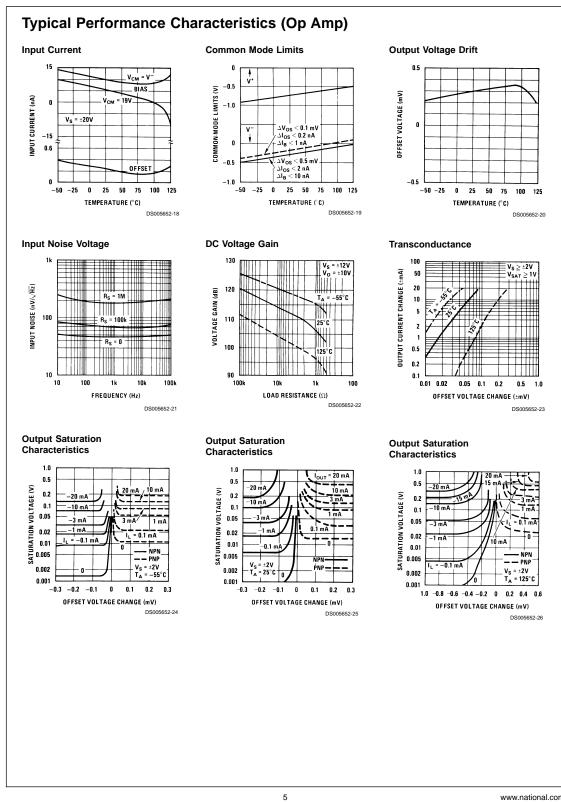
Load regulation: The change in reference output voltage from no load to that load specified.

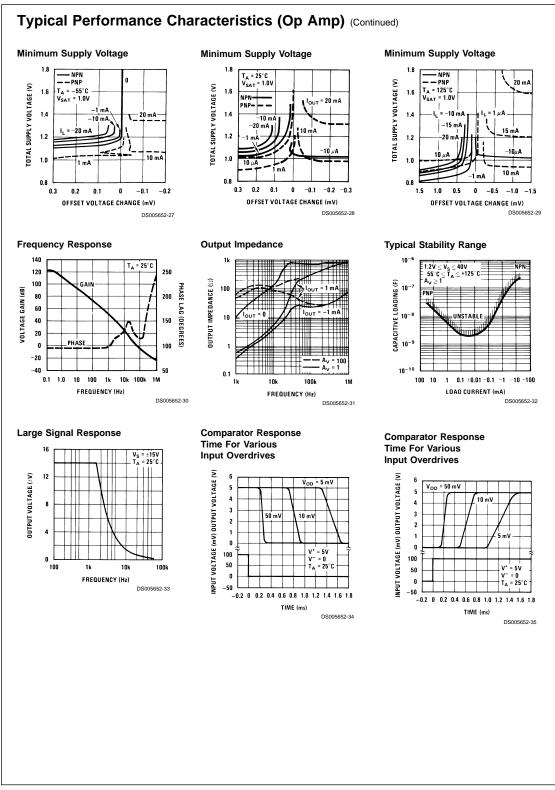
Feedback sense voltage: The voltage, referred to V^- , on the reference feedback terminal while operating in regulation.

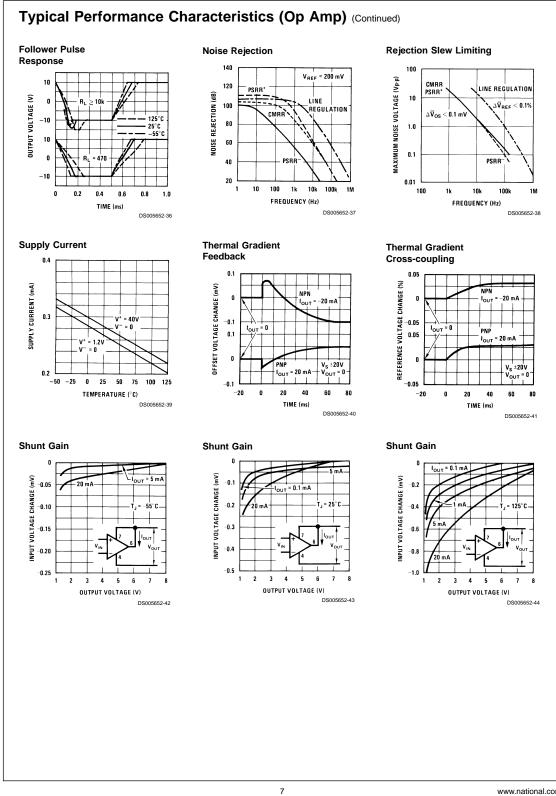
Reference amplifier gain: The ratio of the specified reference output change to the change in feedback sense voltage required to produce it.

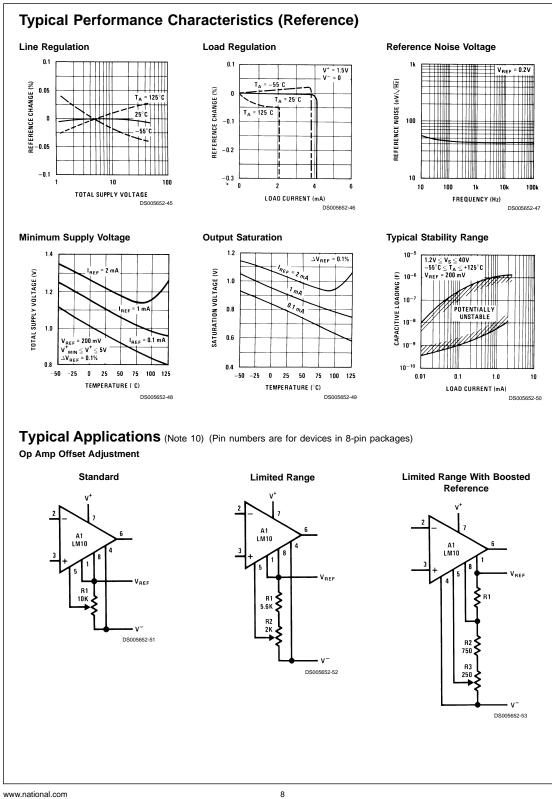
Feedback current: The absolute value of the current at the feedback terminal when operating in regulation.

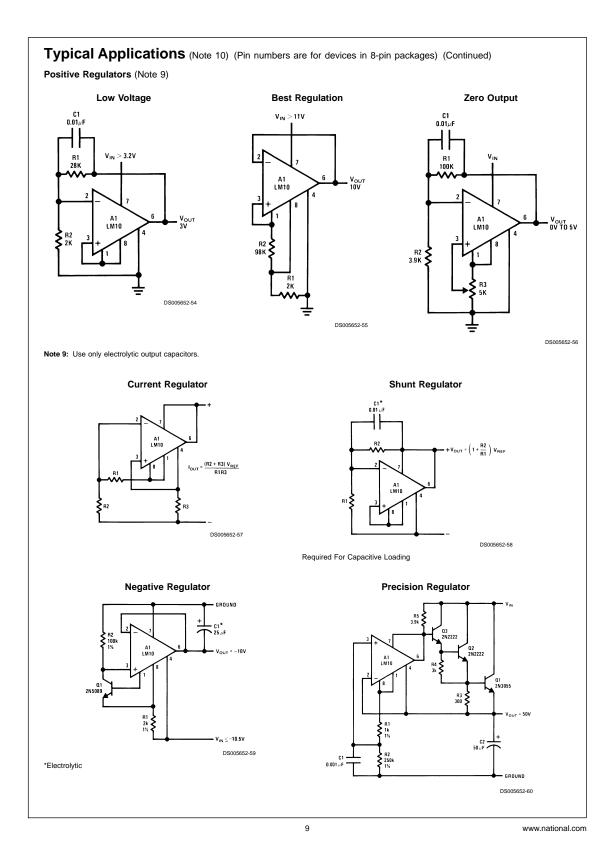
Supply current: The current required from the power source to operate the amplifier and reference with their outputs unloaded and operating in the linear range.



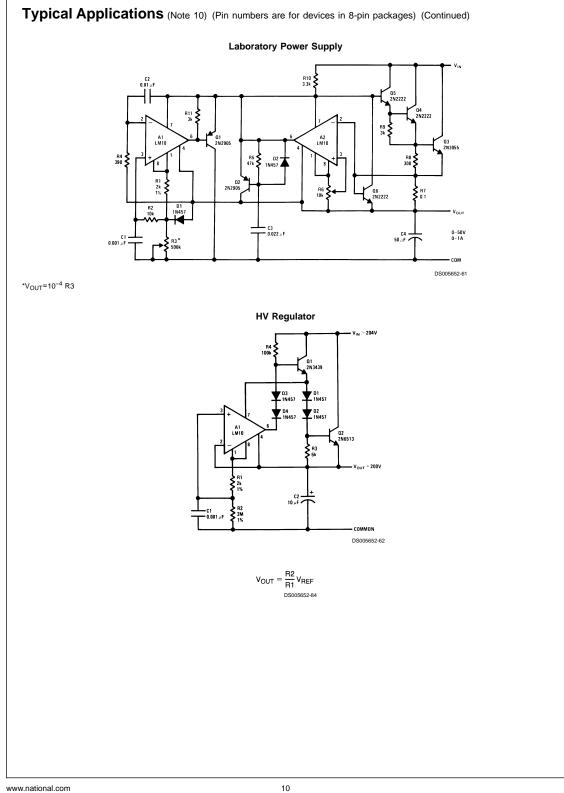


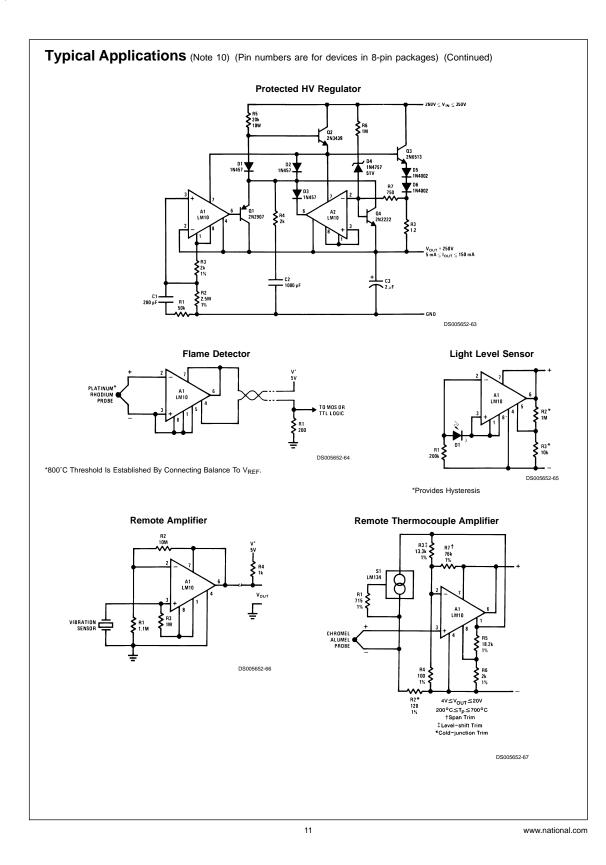


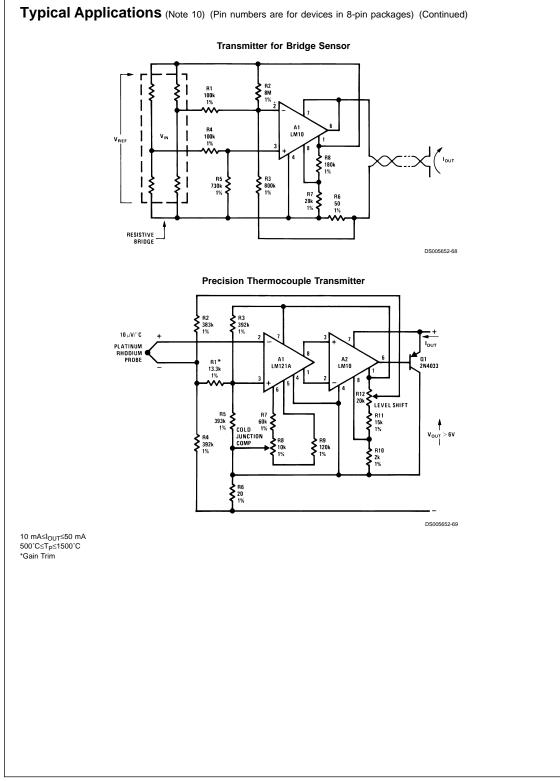


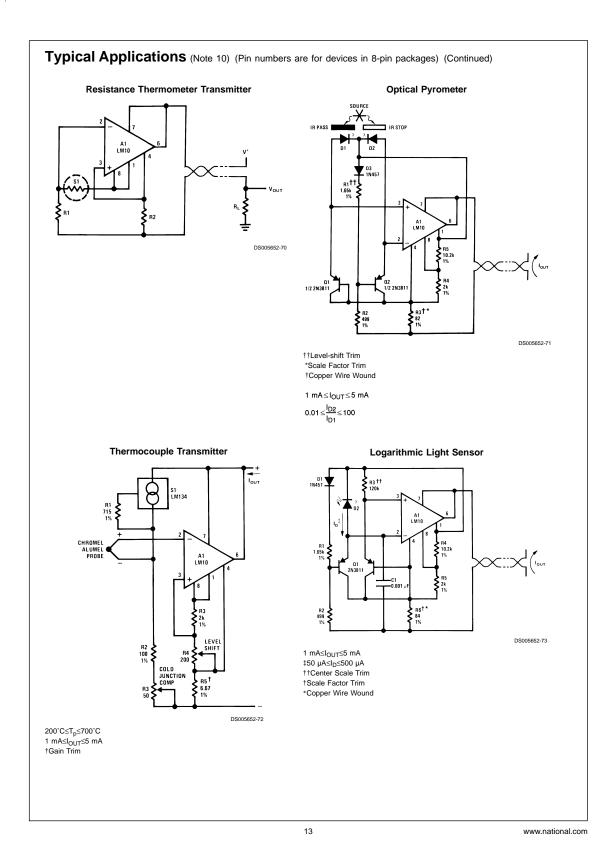


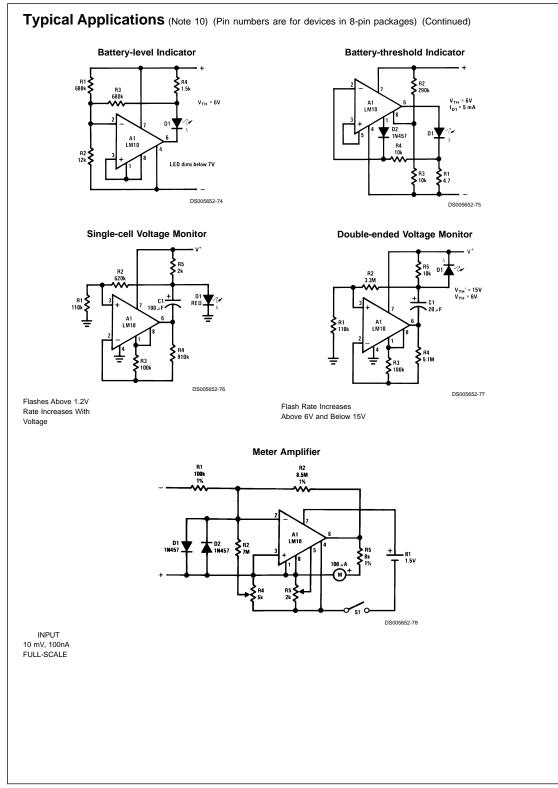
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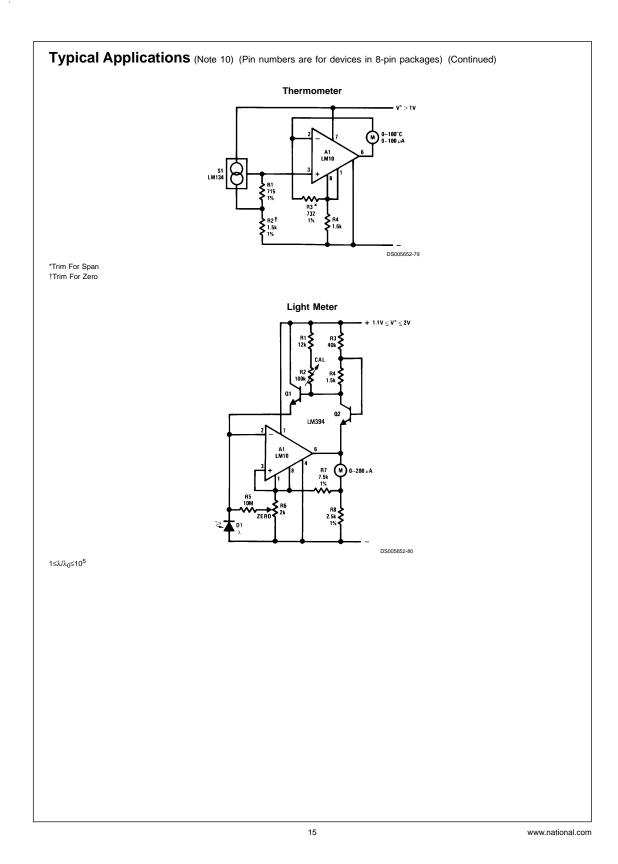


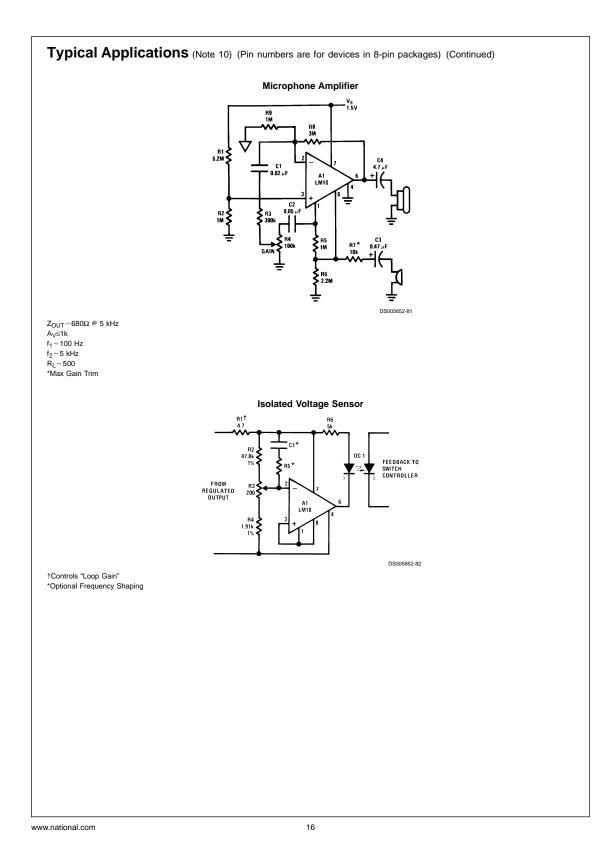




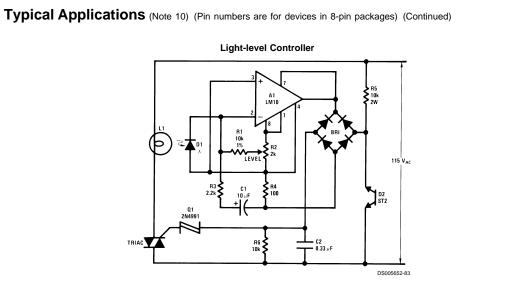








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Note 10: Circuit descriptions available in application note AN-211.

Application Hints

With heavy amplifier loading to V⁻, resistance drops in the V⁻ lead can adversely affect reference regulation. Lead resistance can approach 1 Ω . Therefore, the common to the reference circuitry should be connected as close as possible to the package.

